

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = -140 V
- Complementary to 2STC4468
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Applications

■ Audio power amplifier

Description

This device is an PNP transistor manufactured using BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor exhibits good gain linearity behavior. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stages.

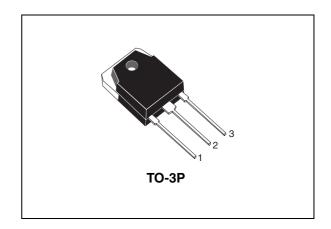


Figure 1. Internal schematic diagram

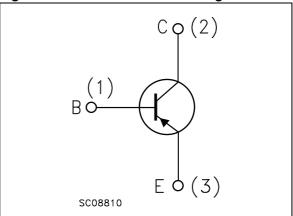


Table 1. Device summary

Order code	Marking	Package	Packaging
2STA1695	2STA1695	TO-3P	Tube

Electrical ratings 2STA1695

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-140	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	-140	V
V _{EBO}	Emitter-base voltage (I _C = 0)	-6	V
I _C	Collector current	-10	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-20	Α
P _{tot}	Total dissipation at T _c = 25 °C	100	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.25	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	35.7	°C/W

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = -140 V			-0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = -6 V			-0.1	μΑ
V _{(BR)CEO}	Collector-emitter breakdown voltage (I _B = 0)	I _C = -50 mA	-140			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μA	-140			V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = -1 mA	-6			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = -5 \text{ A}$ $I_B = -500 \text{ mA}$ $I_C = -7 \text{ A}$ $I_B = -700 \text{ mA}$			-0.5 -0.7	V V
V _{BE} ⁽¹⁾	Base-emitter voltage	$V_{CE} = -5 \text{ V}$ $I_{C} = -5 \text{ A}$			-1.3	V
h _{FE}	DC current gain	$I_{C} = -3 \text{ A}$ $V_{CE} = -4 \text{ V}$ $I_{C} = -5 \text{ A}$ $V_{CE} = -4 \text{ V}$	70 50		140	
f _T	Transition frequency	$I_C = -0.5 \text{ A}$ $V_{CE} = -12 \text{ V}$		20		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = -10 V		225		pF
	Resistive load					
t _{on}	Turn-on time	$I_C = -5 \text{ A}$ $V_{CC} = -60 \text{ V}$		0.24		μs
t _{stg}	Storage time	$I_{B1} = -I_{B2} = -0.5 \text{ A}$		1.2		μs
t _f	Fall time			0.24		μs

^{1.} Pulsed: Pulse duration = 300 $\mu s,\,duty\,cycle \leq~1.5~\%$

Electrical characteristics 2STA1695

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Power derating versus temperature

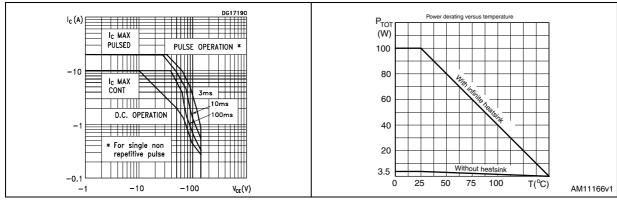


Figure 4. Output characteristics

Figure 5. DC current gain

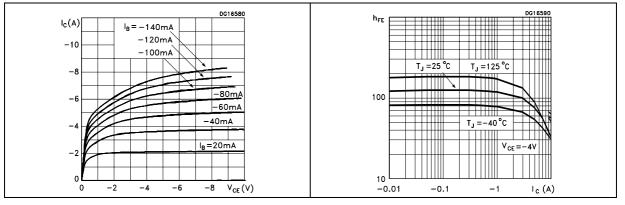


Figure 6. Collector-emitter saturation voltage Figure 7. Base-emitter voltage

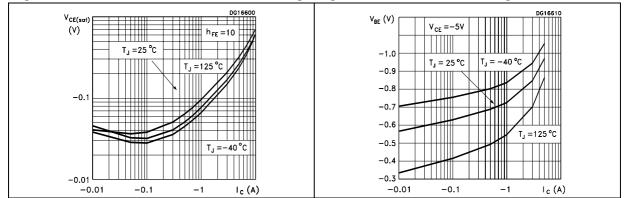
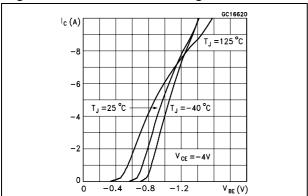
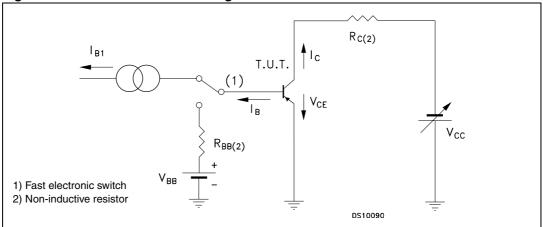


Figure 8. Base-emitter voltage



2.2 Test circuit

Figure 9. Resistive load switching test circuit



3 Package mechanical data

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Table 5. TO-3P mechanical data

Dim.	mm			
	Min.	Тур.	Мах	
А	4.60		5	
A1	1.45	1.50	1.65	
A2	1.20	1.40	1.60	
b	0.80	1	1.20	
b1	1.80		2.20	
b2	2.80		3.20	
С	0.55	0.60	0.75	
D	19.70	19.90	20.10	
D1		13.90		
E	15.40		15.80	
E1		13.60		
E2		9.60		
е	5.15	5.45	5.75	
L	19.50	20	20.50	
L1		3.50		
L2	18.20	18.40	18.60	
øΡ	3.10		3.30	
Q		5		
Q1		3.80		

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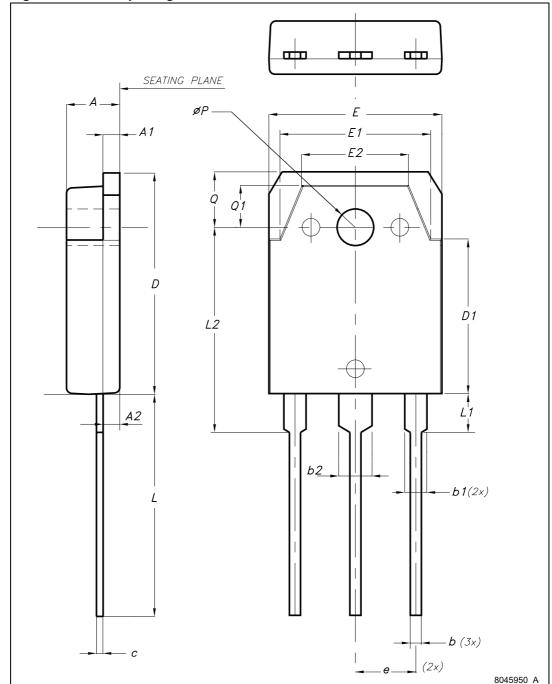


Figure 10. TO-3P package dimensions

2STA1695 Revision history

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
18-May-2007	1	Initial release
06-Nov-2008	2	Document status promoted from preliminary data to datasheet.
07-Feb-2012	3	Figure 3 insertedMechanical data updated

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